

APX-ExVInG-Φ2-PSD-131

450-1700nm Extended Visible InGaAs Position Sensitive Detector

The APX-ExVInG-Φ2-PSD-131 is a high sensitivity, low noise, 2mm diameter active area EXTENDED VISIBLE (ExV) InGaAs position sensitive detector for applications at Visible, NIR, and SWIR wavelengths range. This best-in-class device has a sensitivity from 450 nm to 1700 nm compared to standard InGaAs spectral response of 700 nm to 1700 nm. The photodetector features over 2 kΩ inter electrode resistance and is assembled in a hermetically sealed TO-5 package.

Applications

Alignment

Position Sensing

Medical

Industrial

Nulling

Centering

Targeting

Guidance Systems

Features

High Position Detection Accuracy

450-1700 nm sensitivity

High Inter-electrode resistance

High Shunt Resistance

Low Capacitance

High Sensitivity

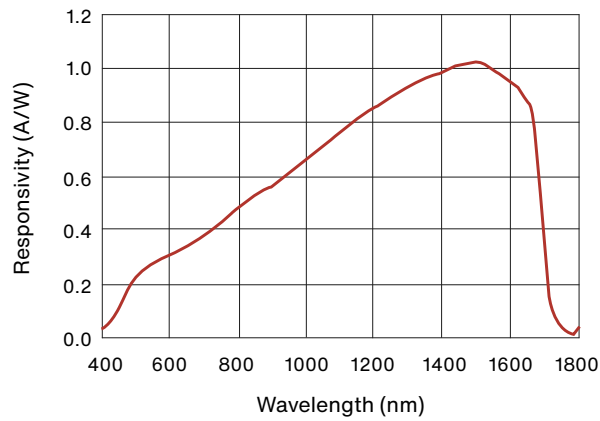
Absolute Maximum Ratings

Parameter	Symbol	Min	Max	Unit
Reverse Voltage	V_R	-	10	V
Operating Temperature	T_{OP}	-40	+125	°C
Storage Temperature	T_{STG}	-55	+125	°C
Package	TO-5			

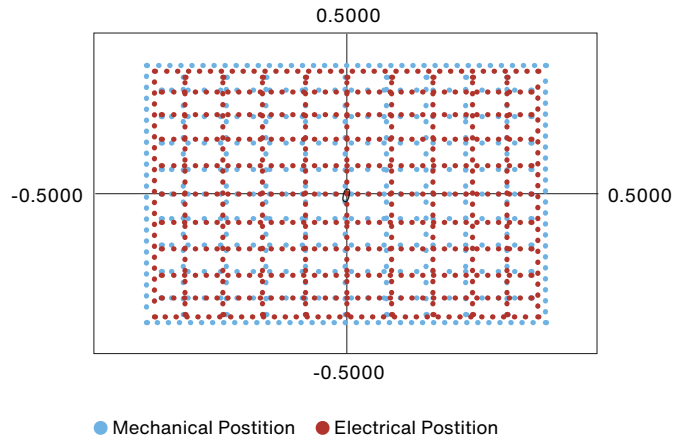
Typical Electro-Optical Specifications at $T_A=23\text{ °C}$

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Active Area Dimension	-	$A.A._D$	-	$\Phi 2$	-	mm
Active Area	-	$A.A.$	-	3.14	-	mm ²
Spectral Range	-	-	400	-	1700	nm
Responsivity	$\lambda=632\text{nm}$	R_λ	0.29	0.32	-	A/W
	$\lambda=1060\text{nm}$	R_λ	0.68	0.72	-	A/W
	$\lambda=1550\text{nm}$	R_λ	0.93	0.98	-	A/W
Capacitance	$V_R=0\text{V}; f=1\text{MHz}$	C_J	-	300	-	pF
	$V_R=5\text{V}; f=1\text{MHz}$	C_J	-	150	-	pF
Dark Current	$V_R=1\text{V}$	I_d	-	10	100	nA
	$V_R=5\text{V}$	I_d	-	20	200	nA
Shunt Resistance	$V_R=10\text{mV}$	R_{SH}	10	25	-	M Ω
Inter-Electrode Resistance	Between diagonally opposing contacts	-	-	2.2	-	K Ω
Position Detection Error	$V_R=1\text{V}$	PDE	-	20	-	μm

Spectral Response

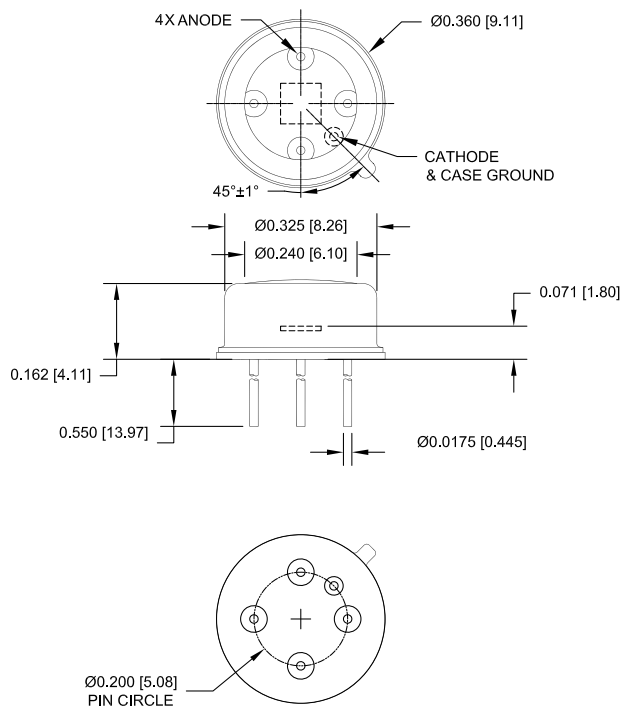


Position Error Scan



Mechanical Specifications

Units are in inches [mm]





APX-ExVInG-Φ0.3-101

450-1700 nm Extended Visible InGaAs Photodiode

APX-ExVInG-Φ0.3-101 is a high sensitivity, low noise, 0.3 mm diameter active area EXTENDED VISIBLE (ExV) InGaAs detector for applications at Visible, NIR, and SWIR wavelengths range. This best-in-class device has a sensitivity from 450 nm to 1700 nm compared to standard InGaAs spectral response of 700 nm to 1700 nm. The photodiode is assembled in a hermetically sealed TO-46 package.

Applications

Industrial Sensing
Security and Defense
Communication

Features

Low Dark Current and Capacitance
High Sensitivity
450-1700 nm sensitivity

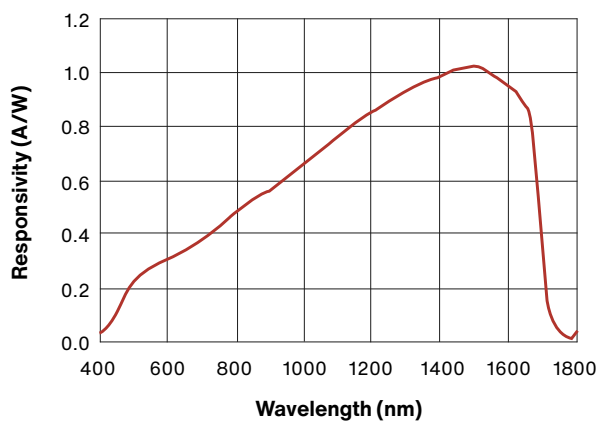
Absolute Maximum Ratings

Parameter	Symbol	Min	Max	Unit
Reverse Voltage	V_R	-	20	V
Operating Temperature	T_{OP}	0	+85	°C
Storage Temperature	T_{STG}	-25	+85	°C
Package	TO-46			

Typical Electro-Optical Specifications at $T_A=23\text{ °C}$

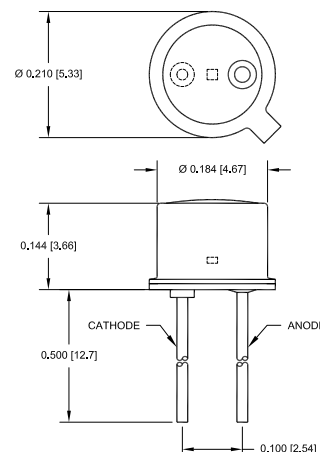
Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Breakdown Voltage	$I_R=100\mu A$	V_{BR}	10	-	-	V
Responsivity	$\lambda=600nm$	R_λ	0.3	0.35	-	A/W
	$\lambda=1064nm$	R_λ	-	0.77	-	A/W
	$\lambda=1200nm$	R_λ	0.7	0.84	-	A/W
	$\lambda=1550nm$	R_λ	0.9	0.93	-	A/W
Shunt Resistance	$V_R=10mV$	R_{SH}	2	20	-	MΩ
Dark Current	$V_R=1V$	I_D	-	2	50	nA
Capacitance	$V_R=1V$; $f=1MHz$	C	-	6	20	pF
Rise Time (50Ω load)	$V_R=5V$; $\lambda=826nm$	T_R	-	5	-	ns
Noise Equivalent Power	$\lambda=900nm$	NEP	-	1.0	-	$10^{-13}W/Hz^{0.5}$

Spectral Response



Mechanical Specifications

Units are in inches (mm)



Care and handling instructions

Your optoelectronic components are packaged and shipped in opaque, padded containers to avoid ambient light exposure and damage due to shock from dropping or jarring.

Care must be taken to avoid exposure to high ambient light levels, particularly from tungsten sources or sunlight.

- These components can be rendered inoperable if dropped or sharply jarred. The wire bonds are delicate and can become separated from the bonding pads when the component is dropped or otherwise receives a sharp physical blow.
- Most windows on photodiodes are either silicon or quartz. They should be cleaned with isopropyl alcohol and a soft (optical grade) pad.
- Photodiode exposure to extreme high or low storage temperatures can affect the subsequent performance. Maintain a non-condensing environment for optimum performance and lifetime.
- All devices are considered ESD sensitive. The photodiodes are shipped in ESD protective packaging. When unpacking and using these products, anti-ESD precautions should be observed.
- Photodiode packages and/or operation may be impaired if exposed to CHLOROETHENE, THINNER, ACETONE, TRICHLOROETHYLENE or any harsh chemicals.
- Optoelectronic components in plastic packages should be given special care. Clear plastic packages are more sensitive to environmental stress than those of black plastic. Storing devices in high humidity can present problems when soldering. Since the rapid heating during soldering stresses the wire bonds and can cause wire to bonding pad separation, it is recommended that devices in plastic packages to be baked for 24 hours at 85°C.
- The leads on the photodiode SHOULD NOT BE FORMED. If your application requires lead spacing modification, please contact Advanced Photonix Applications group at Techsupport@advancedphotonix.com before forming a product's leads. Product warranties could be voided.
- Most devices are provided with wire or pin leads for installation in circuit boards or sockets. Observe the soldering temperatures and conditions specified below:
 - Soldering Iron: Soldering 30 W or less
 - Temperature at tip of iron 300°C or lower.
 - Dip Soldering: Bath Temperature: 260±5°C.
 - Immersion Time: within 5 Sec.
 - Soldering Time: within 3 Sec.
 - Vapor Phase Soldering, Reflow Soldering: DO NOT USE

Legal Disclaimer

Information in this data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.



Most of our standard catalog products are RoHS Compliant. Please contact us for details.

